

AUTOMOTIVE CURRENT TRANSDUCER HC5F800-S









Introduction

The HC5F family is for the electronic measurement of DC, AC or pulsed currents in high power and low voltage automotive applications with galvanic isolation between the primary circuit (high power) and the secondary circuit (electronic circuit).

The HC5F family gives you the choice of having different peak currents (from ± 200 A up to ± 900 A) in the same housing.

Features

- · Open Loop transducer using the Hall effect
- Low voltage application
- Unipolar + 5 V DC power supply
- Primary current measuring range up to ± 800 A
- Maximum RMS primary current limited by the busbar, the magnetic core or the ASIC temperature T° < + 150°C
- Operating temperature range: 40°C < T° < + 125°C
- Output voltage: full ratiometric (sensitivity and offset)
- High speed transducer.

Advantages

- Good accuracy
- Good linearity
- Low thermal offset drift
- · Low thermal sensitivity drift.

Automotive applications

- Electrical Power Steering
- Starter Generators
- Converters ...

Principle of HC5F Family

The open loop transducers uses a Hall effect integrated circuit. The magnetic flux density B, contributing to the rise of the Hall voltage, is generated by the primary current $I_{\rm P}$ to be measured.

The current to be measured I_p is supplied by a current source i.e. battery or generator (Fig. 1).

Within the linear region of the hysteresis cycle, B is proportional to:

B
$$(I_p)$$
 = constant (a) $\times I_p$

The Hall voltage is thus expressed by:

$$V_{\perp} = (R_{\perp}/d) \times I \times constant (a) \times I_{\square}$$

Except for $\mathbf{I}_{\mathrm{p}},$ all terms of this equation are constant. Therefore:

$$V_{H}$$
 = constant (b) x I_{P}

The measurement signal $\mathbf{V}_{\rm H}$ amplified to supply the user output voltage or current.

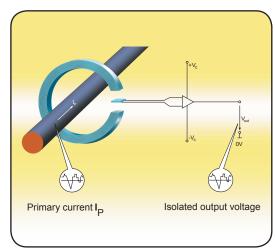


Fig. 1: Principle of the open loop transducer



HC5F800-S

Dimensions HC5F800-S family (in mm.)

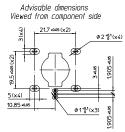


Secondary connection

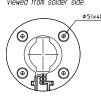
Terminals	Designations			
3	Supply voltage + 5 V DC			
1	V _{OUT}			
2	Ground			
E1 to E4	Ground (*)			

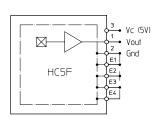
(*) Only 1 of these 4 pins could be connected

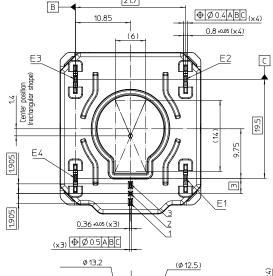
PCB DRILLING (scale 1:1)

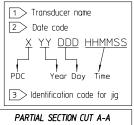


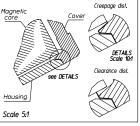
Advisable dimensions Viewed from solder side

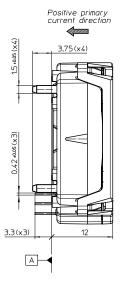












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Bill of materials

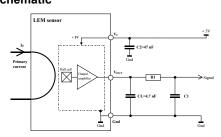
Plastic case
 Magnetic core
 Pins
 Copper alloy base tin plated (lead free)
 Mass

als Remarks

General tolerance ± 0.2 mm
 V_{CUT} > V_C when I_D flows in the

• $V_{OUT} > \frac{V_c}{2}$ when I_p flows in the direction of the arrow.

Electronic schematic



 $\mathbf{R}_{\text{LOAD}} > 10 \text{ K}\Omega$

 $\mathbf{C}_{\text{LOAD}}^{\text{----}}$ Nominal value 4.7 nF ± 10 %

 $(C_{\mathsf{LQAD}}$ is obligation to stabilize and to avoid the ondulation of the output signal)

R₁**C**₁ low pass filter EMC protection (optional)

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Absolute maximum ratings (not operating)

Parameter	Symbol	Unit	Specification			Conditions
			Min	Typical	Max	
Supply over voltage	V	V			7	No operating, 1 min@ 25°C
Reverse voltage	V _C	V	V Not applicable		No operating	
Output over voltage	V _{out}	V	- 0.5		V _c + 0.5	No operating
Continuous output current	lout	mA	- 10		10	No operating
Output short-circuit duration	t _c	min			2	
Maximum admissible vibration	γ	m.s ⁻²			200	ISO 16750-3&4.1.2.1.2.1
Rms voltage for AC insulation test 50 Hz, 1 min	V _d	kV			1.2	IEC 60664 Part 1
Electrostatic discharge voltage	V _{ESD}	kV			2	JESD22-A114-B
Ambient storage temperature	T _s	°C	- 55		150	tested after 64H @-55°C connected
Clearance distance	dCI	mm		1.2		
Creepage distance	dCp	mm		1.65		

Operating characteristics

Parameter	Symbol	Unit	S	pecificatio	n	Conditions
	Symbol		Min	Typical	Max	Conditions
		Electri	cal Data			
Primary current, measuring range	I _P	Α	- 800		800	
Supply voltage 1)	V _c	V	4.75	5.00	5.25	
Output voltage (Analog)	V _{OUT}	V	V _{OUT} = (V _O	/5) x (2.5 +0.	0025 x I _P)	@ v _c
Sensitivity	G	mV/A		2.5		@ V _C = 5 V
Current consumption	I _c	mA		12	20	
Load resistance	R _L	ΚΩ	10			
Capacitive loading	C _L			4.7		
Output internal resistance	R _{OUT}	Ω			10	
Ambient operating temperature	T _A	°C	- 40		125	
	·	Performa	nce Data ⁽¹⁾)		•
Sensitivity error	$\epsilon_{_{ m G}}$	%	- 2		2	$\textcircled{0}$ $\mathbf{T}_{A} = 25^{\circ}\text{C}; \mathbf{V}_{C} = 5 \text{ V}$
Electrical offset	I _{OE}	Α	- 3	± 1.5	3	T _A = 25°C
Magnetic offset	I _{OM}	Α	- 2.2	± 1.5	2.2	@ After excursion to $\pm I_p$; $T_A = 25^{\circ}C$
Offset current	I _o	Α	- 4		4	T _A = 25°C
Average temperature coefficient of I _{OE}	TCI _{OEAV}	mA/°C	-34	± 8	34	@ - 40°C < T° < 125°C; V _C
Average temperature coefficient of G	TCG _{AV}	%/°C	-0.050	± 0.025	0.050	@ - 40°C < T° < 125°C; V _C
Linearity error	ε,	% IP	-1		1	Of full range
Response time	t,	μs		5	10	
Frequency bandwidth 2)	BW	kHz	30			@ - 3 dB
Output voltage low	V _{OUTL}	V	0.1			@ V _c = 5 V
Output voltage high	V _{OUTH}	V			4.9	@ V _c = 5 V
Output voltage noise peak-peak	V _{no p-p}	mV			17	DC to 1 MHz
Output voltage noise rms	V _{no rms}	mV			2.6	DC to 1 MHz

Notes:
1) The output voltage \mathbf{V}_{OUT} is fully ratiometric. The offset and sensitivity are dependent on the supply voltage \mathbf{V}_{C} relative to the following formula: $I_{\text{P}} = \left(V_{\text{OUT}} - \frac{V_{\text{C}}}{2}\right) \times \frac{1}{G} \times \frac{5}{V_{\text{C}}} \qquad \text{with } G \text{ in } (\text{V/A})$

$$I_P = \left(V_{\text{OUT}} - \frac{V_c}{2}\right) \times \frac{1}{G} \times \frac{5}{V_c}$$
 with G in (V/A)

²⁾ Small signal only to avoid excessive heating of the busbar, the magnetic core and the ASIC.



HC5F800-S

PERFORMANCES PARAMETERS DEFINITIONS

Output noise voltage:

The output voltage noise is the result of the noise floor of the Hall elements and the linear I_c amplifier gain.

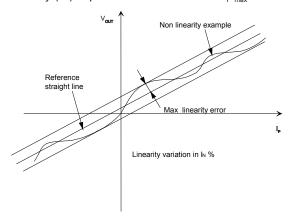
Magnetic offset:

The magnetic offset is the consequence of an over-current on the primary side. It's defined after an excursion of $I_{P,max}$.

Linearity:

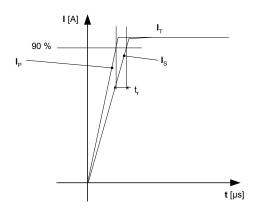
The maximum positive or negative discrepancy with a reference straight line $V_{\text{OUT}} = f(I_p)$.

Unit: linearity (%) expressed with full scale of I_{P max}.



Response time (delay time) t,:

The time between the primary current signal and the output signal reach at 90 % of its final value



Typical:

Theorical value or usual accuracy recorded during the production.

Sensitivity:

The Transducer's sensitivity **G** is the slope of the straight line $V_{out} = f(I_p)$, it must establish the relation:

 $V_{out}(I_{p}) = V_{c}/5 (G \times I_{p} + 2.5) (*)$

(*) For all symetrics transducers.

Offset with temperature:

The error of the offset in the operating temperature is the variation of the offset in the temperature considered with the initial offset at 25°C.

The offset variation I_{OT} is a maximum variation the offset in the temperature range:

 $I_{OT} = I_{OF} \max - I_{OF} \min$

The Offset drift $\mathbf{TCI}_{\text{OEAV}}$ is the \mathbf{I}_{OT} value divided by the temperature range.

Sensitivity with temperature:

The error of the sensitivity in the operating temperature is the relative variation of sensitivity with the temperature considered with the initial offset at 25° C.

The sensitivity variation \mathbf{G}_{T} is the maximum variation (in ppm or %) of the sensitivity in the temperature range:

 \mathbf{G}_{T} = (Sensitivity max - Sensitivity min) / Sensitivity at 25°C.

The sensitivity drift \mathbf{TCG}_{AV} is the \mathbf{G}_{T} value divided by the temperature range.

Offset voltage @ $I_p = 0$ A:

Is the output voltage when the primary current is null. The ideal value of \mathbf{V}_{O} is $\mathbf{V}_{\text{C}}/2$ at \mathbf{V}_{C} = 5 V. So, the difference of \mathbf{V}_{O} - $\mathbf{V}_{\text{C}}/2$ is called the total offset voltage error. This offset error can be attributed to the electrical offset (due to the resolution of the ASIC quiescent voltage trimming), the magnetic offset, the thermal drift and the thermal hysteresis.

Environmental test specifications

NAME	STANDARD	CONDITIONS			
ENVIRONMENTAL TESTS					
Thermal shocks	IEC 60068-2-14 test Na (01/2009)	T° - 40°C to 125°C / 30 mn each, 300 cycles not connected			
T° humidity cyclic	ISO 16750-4	10 cycles of 24H, high T°, power supply on monitored			
Power temp cycle	IEC 60068 Part 2-14 test Nb (01/2009)	T° - 40°C to 125°C, 15 mn/step, transition time 15 mn 600 cycles			
Temperature humidity bias	JESD22-A101 (04/97)	T° 85°C / 85 % RH/ 1000 H power supply on, monitored each 6H			
MECHANICAL TESTS					
Sinus vibration	ISO 16750-3 & 4.1.2.1.2.1 (08/2007)	No power supply- profile 1 f = 100 to 1000 Hz, g = 100 to 200 m/s², 22H/axis 3 axis, T°C cycle -40°C to 125°C			
Random vibration	IEC 60068-2-64 (02/2008)	No power supply g rms = 27.8 m/s², f = 10 Hz 1 kHz, PSD = 0.14 to 20 (m/s²) ²/Hz 12H/axis and Y, 36 H for axis Z, T°C. cycle -40°C to 125			
Stocks	IEC 60068-2-27 (02/2008)	Half sine shocks @ 25°C, 25 g/ 15 ms, 132 shocks/direction, 6 directions, 100 g/11 ms, 3 shock/direction, 6 directions			
Drop test	ISO 16750-3& 4.3 (08/2007)	Drop 1 m, 2 falls/part, 1 part/axis, 6 directions parts without PCB			
ELECTRICAL TESTS					
Rms voltage for AC isolation test	IEC 60664-1	1.2 kV/50 Hz/1 mn			
Isolation resistance	ISO 16750-2& 4.10	500 V DC, 25°C, R isolation > 10 MOhms			
EMC TESTS					
Electrostatic discharge	IEC 61000-4-2	Contact ± 2 kV , air ± 2 kV			
Electrostatic discharge	JESD22-A114-B	HBM: 1.5 kOhms / 100 pF 2kV			